

描述 / Descriptions

TO-92 塑封封装 NPN 半导体三极管。Silicon NPN transistor in a TO-92 Plastic Package.

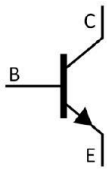
特征 / Features

与 2SA1029 互补。
Complementary pair with 2SA1029.

用途 / Applications

用于低频低噪声放大。
Low frequency low noise amplifier.

内部等效电路 / Equivalent Circuit



引脚排列 / Pinning



PIN1 : Base PIN 2 : Collector PIN 3 : Emitter

放大及印章代码 / hFE Classifications & Marking

h _{FE} Classifications Symbol	B	C
h _{FE} Range	100~200	160~320

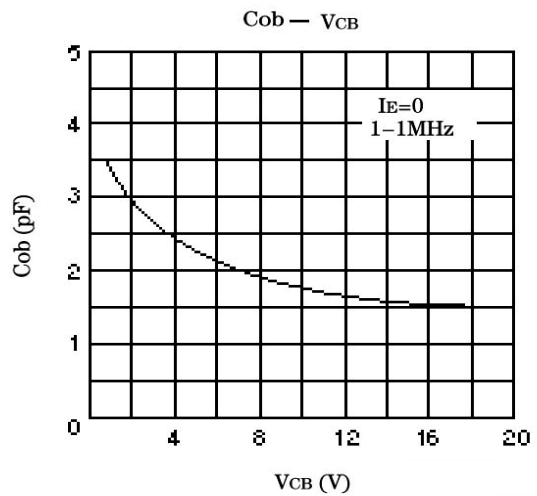
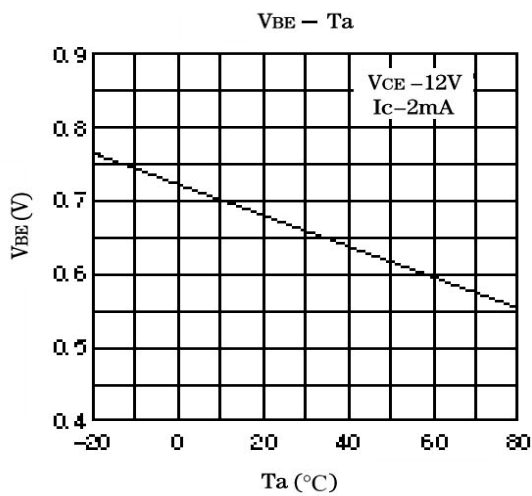
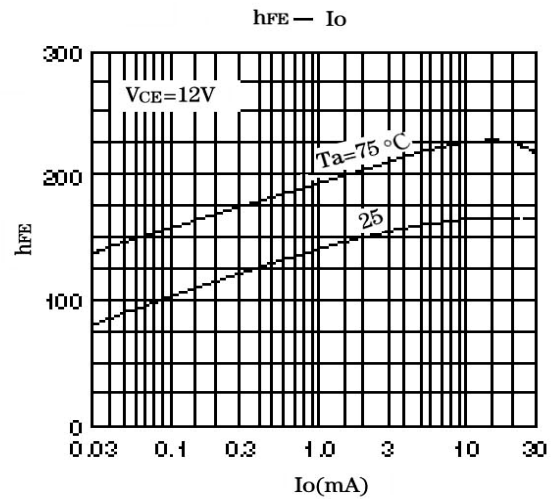
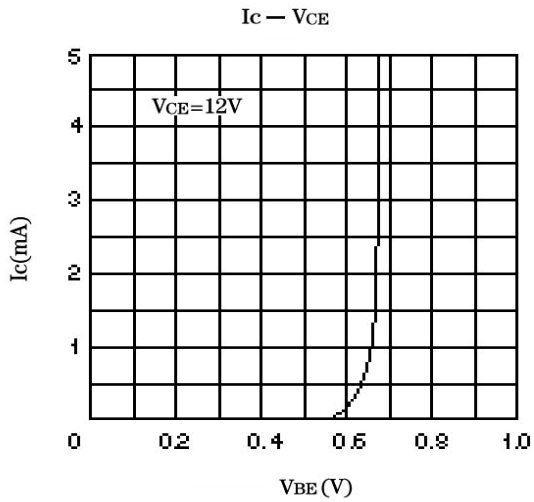
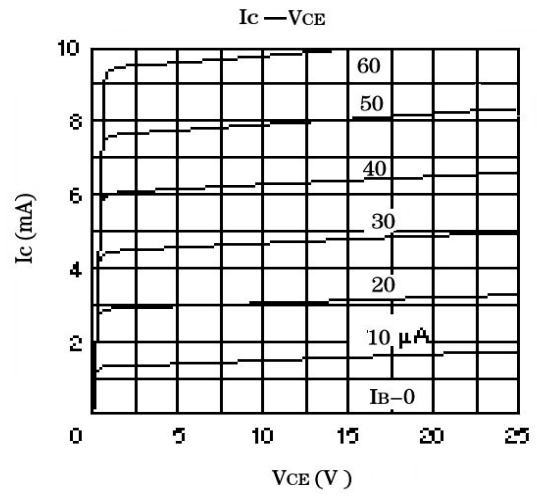
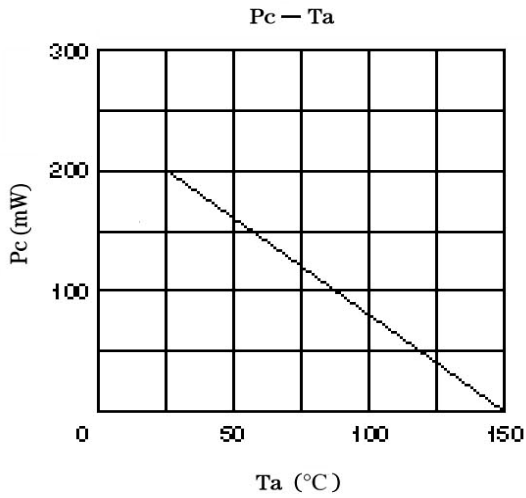
极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Collector to Base Voltage	V_{CBO}	55	V
Collector to Emitter Voltage	V_{CEO}	50	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	100	mA
Emitter Current - Continuous	I_E	-100	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C

电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=10\mu A$ $I_E=0$	55			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=1.0mA$ $R_{BE}=\infty$	50			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=10\mu A$ $I_C=0$	5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=18V$ $I_E=0$			0.5	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=2.0V$ $I_C=0$			0.5	μA
DC Current Gain	h_{FE}	$V_{CE}=12V$ $I_C=2.0mA$	100		320	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=10mA$ $I_B=1.0mA$			0.2	V
Base to Emitter Voltage	V_{BE}	$V_{CE}=12V$ $I_C=2.0mA$		0.67	0.75	V
Transition Frequency	f_T	$V_{CE}=12V$ $I_C=2.0mA$		230		MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10V$ $I_E=0$ $f=1.0MHz$		1.8	3.5	pF
Noise Figure	NF	$V_{CE}=6.0V$ $I_C=0.1mA$ $f=120Hz$ $R_g=500\Omega$		3.0	5.0	dB
Small Signal Input Impedance	h_{ie}	$V_{CE}=5.0V$ $I_C=0.1mA$ $f=270Hz$		16.5		K Ω
Small Signal Voltage Feedback Ratio	h_{re}	$V_{CE}=5.0V$ $I_C=0.1mA$ $f=270Hz$		70		$\times 10^{-6}$
Small Signal Current Transfer Ratio	h_{fe}	$V_{CE}=5.0V$ $I_C=0.1mA$ $f=270Hz$		130		
Small Signal Output Admittance	h_{oe}	$V_{CE}=5.0V$ $I_C=0.1mA$ $f=270Hz$		11		μS

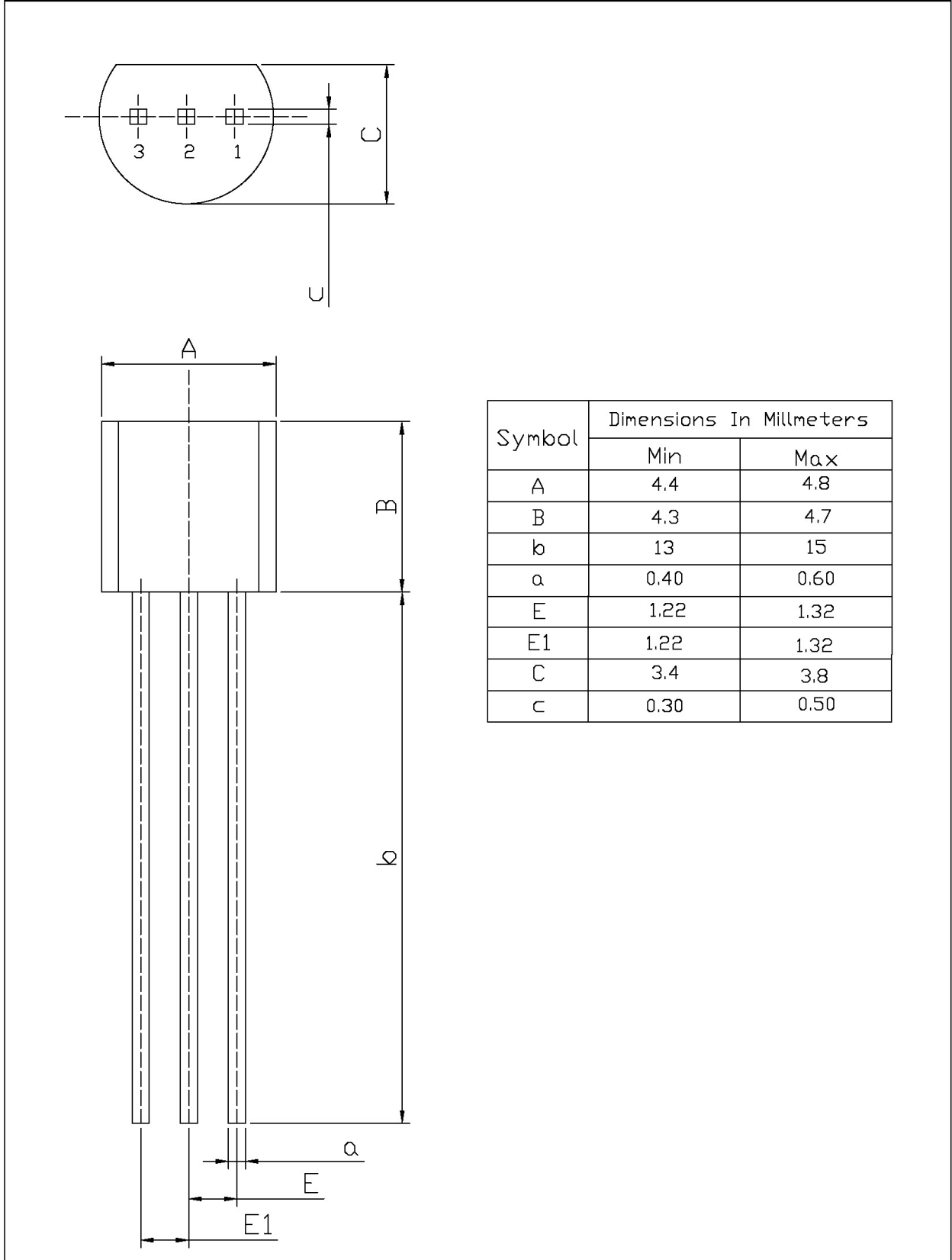
电参数曲线图 / Electrical Characteristic Curve



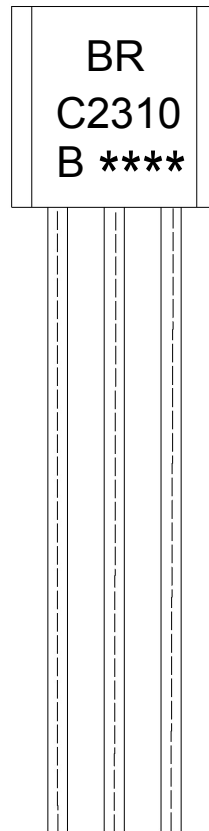
外形尺寸图 / Package Dimensions

TO-92

Unit: mm



印章说明 / Marking Instructions



说明：

BR: 为公司代码

C2310 : 为型号代码

B: 为 h_{FE} 分档代码

**** : 为生产批号代码，随生产批号变化。

Note:

BR: Company Code.

C2310: Product Type.

B: h_{FE} Classifications Symbol

****: Lot No. Code,code change with Lot No.

波峰焊温度曲线图(无铅) / Temperature Profile for Dip Soldering(Pb-Free)



说明：

- 1、预热温度 25 ~ 150°C，时间 60 ~ 90sec;
- 2、峰值温度 255±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2 ~ 10°C/sec.

Note:

- 1.Preheating:25~150°C, Time:60~90sec.
- 2.Peak Temp.:255±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：270±5°C

时间：10±1 sec.

Temp:270±5°C

Time:10±1 sec

包装规格 / Packaging SPEC.

散件包装 / BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)		
	Units/Bag 只/袋	Bags/Inner Box 袋/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Bag 袋	Inner Box 盒	Outer Box 箱
TO-92	1,000	10	10,000	5	50,000	135×190	237×172×102	560×245×195
	1,000	10	10,000	10	100,000	135×190	237×172×102	560×245×375

编带包装 / AMMO

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)	
	Units/tape 只/纸带	Tape/Inner Box 纸带/盒	Rows/Inner Box 纸带层/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Inner Box 盒	Outer Box 箱
TO-92	3,000	1	120	10	30,000	328×230×42	小箱 480×346×235, 大箱 547×407×268

使用说明 / Notices